the first conductivity type is a p-type conductor; and the second conductivity type is a n-type conductor.

8. (Amended) The semiconductor device of claim 5, wherein, the first conductivity type is a n-type conductor; and the second conductivity type is a p-type conductor.

9. (Amended) The method of claim 5, wherein a first conductive well area and a second conductive well area are separately formed within the deep well area.

10. (Amended) The method of claim 9, wherein the first conductive well area is formed of the first conductivity type; and the second conductive well area is formed of the second conductivity type.

11. (Amended) The method of claim 6, wherein the scribe lanes are formed at all portions surrounding the chip formation areas.

12. (Amended) The method of claim 6, further comprising removing the mask using plasma processing or plasma equipment.